RGC80TSX8R

1800V 40A Field Stop Trench IGBT

Datasheet

V _{CES}	1800V
I _{C (100°C)}	40A
V _{CE(sat) (Typ.)}	2.2V
P_D	535W

Outline TO-247N

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Monolithic Body Diode

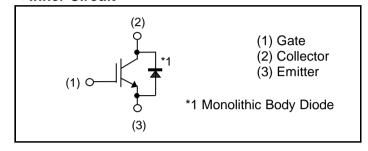
with Low Forward Voltage

5) Pb - free Lead Plating; RoHS Compliant

Application

Voltage - resonance Inverter ΙH

●Inner Circuit



Packaging Specifications

	Packaging	Tube			
	Reel Size (mm)	-			
Type	Tape Width (mm)	-			
Туре	Basic Ordering Unit (pcs)	450			
	Packing Code	C11			
	Marking	RGC80TSX8R			

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	1800	V
Gate - Emitter Voltage		V _{GES}	±30	V
Callagton Cummant	T _C = 25°C	I _C	80	Α
Collector Current	T _C = 100°C	I _C	40	Α
Pulsed Collector Current	I _{CP} *1	120	Α	
D: 1 5 10 1	T _C = 25°C	I _F	80	Α
Diode Forward Current	T _C = 100°C	l _F	40	Α
Diode Pulsed Forward Current		I _{FP} *1	80	Α
$T_C = 25^{\circ}C$		P _D	535	W
Power Dissipation	T _C = 100°C	P _D	267	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiailielei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.28	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	0.28	°C/W

●IGBT Electrical Characteristics (at T_i = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	oditions		Values		
r arameter	Symbol Conditions -		Min.	Тур.	Max.	Unit	
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	1800	ı	ı	V	
Collector Cut - off Current	I _{CES}	V _{CE} = 1860V, V _{GE} = 0V	ı	ı	10	μΑ	
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	ı	ı	±200	nA	
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 120.7 \text{mA}$	5.0	6.0	7.0	V	
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = 40A, V_{GE} = 15V$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$		2.2 2.9	5.0 -	V	

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit	
- Farameter	Symbol	Symbol		Тур.	Max.	Offic	
Input Capacitance	C _{ies}	$V_{CE} = 30V$	-	9550	-		
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	115	-	pF	
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	102	-		
Total Gate Charge	Q_g	V _{CE} = 600V	-	468	-		
Gate - Emitter Charge	Q_ge	I _C = 40A	-	93	-	nC	
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	155	-		
Turn - on Delay Time	t _{d(on)}	$I_C = 40A$, $V_{CC} = 600V$, $V_{GE} = 15V$, $R_G = 10\Omega$, $T_j = 25^{\circ}C$ Inductive Load *E _{on} include diode reverse recovery	-	80	-		
Rise Time	t _r		-	53	-	ns	
Turn - off Delay Time	t _{d(off)}		-	565	-		
Fall Time	t _f		-	55	-		
Turn - on Switching Loss	E _{on}		-	1.85	-		
Turn - off Switching Loss	E _{off}		-	1.60	2.15	mJ	
Turn - on Delay Time	t _{d(on)}		-	68	-		
Rise Time	t _r	$I_C = 40A, V_{CC} = 600V,$ $V_{GE} = 15V, R_G = 10\Omega,$ $T_i = 175^{\circ}C$	-	52	-	20	
Turn - off Delay Time	t _{d(off)}		-	670	-	ns	
Fall Time	t _f	Inductive Load	-	55	-		
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	1.95	-	m l	
Turn - off Switching Loss	E _{off}		-	2.00	-	mJ	

●FRD Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Doromotor	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
		$I_F = 40A, V_{GE} = 0V$				
Diode Forward Voltage	V_{F}	T _j = 25°C	-	1.8	2.3	V
		T _j = 175°C	-	2.4	-	

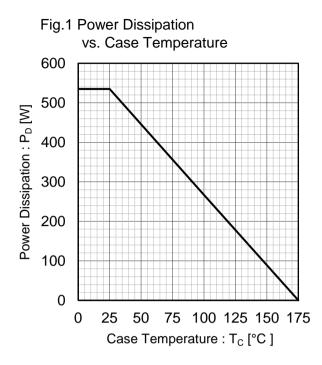


Fig.2 Collector Current vs. Case Temperature 90 80 70 Collector Current : Ic [A] 60 50 40 30 20 T_j ≤ 175°C V_{GE} ≥ 15V 10 0 25 50 75 100 125 150 175 Case Temperature : T_C [°C]

Fig.3 Forward Bias Safe Operating Area 1000 100 Collector Current : I_C [A] 10µs 100µs 10 1 0.1 $T_{\rm C} = 25^{\rm o}{\rm C}$ Single Pulse 0.01 10 100 1000 10000 Collector To Emitter Voltage: V_{CE} [V]

Fig.4 Reverse Bias Safe Operating Area

Fig.5 Typical Output Characteristics

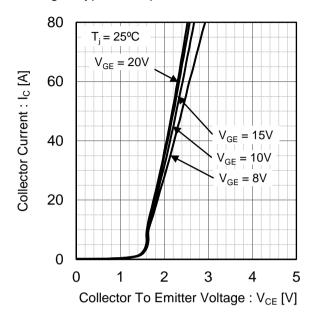


Fig.6 Typical Output Characteristics

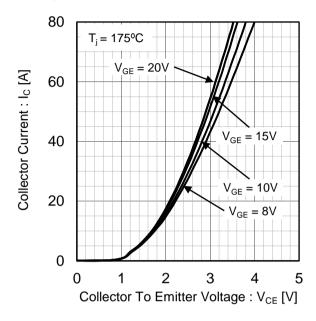


Fig.7 Typical Transfer Characteristics

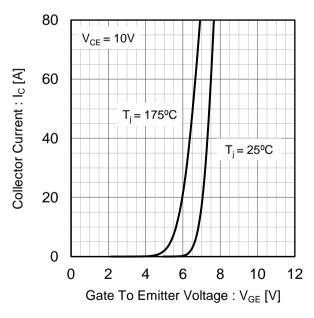
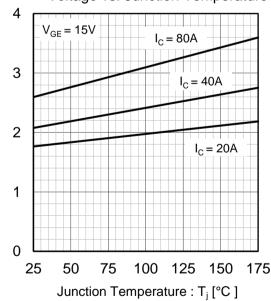


Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature



Collector To Emitter Saturation

Voltage: V_{CE(sat)} [V]

Fig.9 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

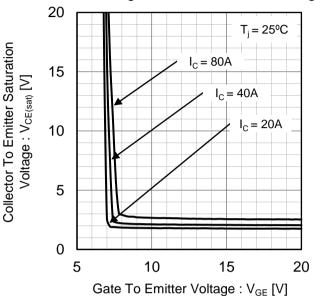
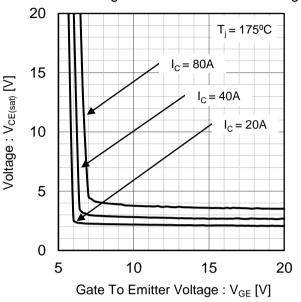


Fig.10 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

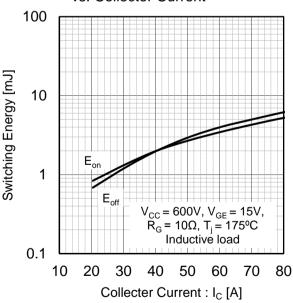


vs. Collector Current 1000 $t_{d(off)}$ 100

Fig.11 Typical Switching Time

Switching Time [ns] 10 V_{CC} = 600V, V_{GE} = 15V, R_G = 10 Ω , T_j = 175°C Inductive load 1 30 10 20 40 50 60 70 80 Collecter Current : I_C [A]

Fig.12 Typical Switching Energy Losses vs. Collector Current



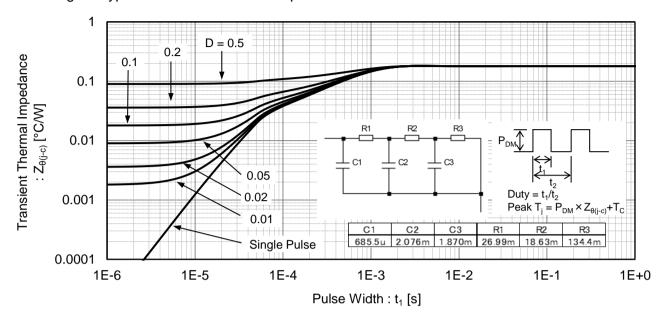
Collector To Emitter Saturation

Fig.13 Typical Capacitance vs. Collector to Emitter Voltage 100000 C_{ies} 10000 Capacitance [pF] $\mathsf{C}_{\mathsf{res}}$ Coes 100 f = 1MHz $V_{GE} = 0V$ $T_j = 25^{\circ}C$ 10 0.01 0.1 1 10 100 Collector To Emitter Voltage : V_{CE} [V]

Fig.14 Typical Gate Charge

Fig.15 Typical Diode Forward Current vs. Forward Voltage 80 Forward Current : I_F [A] 60 $T_i = 25^{\circ}C$ $T_i = 175^{\circ}C$ 40 20 $V_{GE} = 0V$ 0 2 5 0 3 4 Forward Voltage: V_F [V]

Fig.16 Typical Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

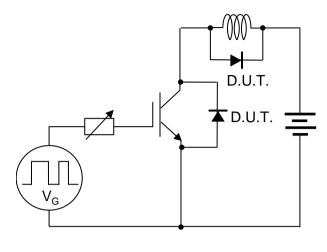


Fig.17 Inductive Load Circuit

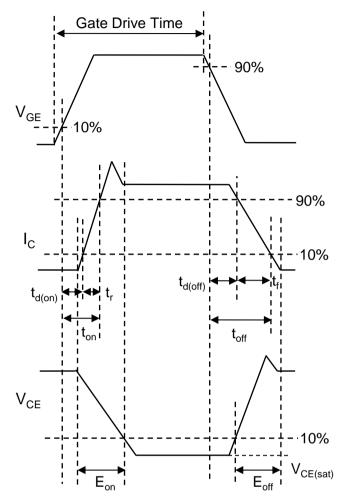


Fig.18 Inductive Load Waveform

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RGC80TSX8R - Web Page

Part Number	RGC80TSX8R
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes